Theory of the oscillatory photoconductivity of a 2D electron gas

I.A. Dmitriev[1,*], M.G. Vavilov[2], I.L. Aleiner[3], A.D. Mirlin[1,4,†], and D.G. Polyakov[1,‡]
[1] Institut für Nanotechnologie, Forschungszentrum Karlsruhe, 76021 Karlsruhe, Germany
[2] Department of Physics, Massachusetts Institute of Technology, Cambridge, MA 02139, USA
[3] Physics Department, Columbia University, New York, NY 10027, USA
[4] Institut für Theorie der Kondensierten Materie, Universität Karlsruhe, 76128 Karlsruhe, Germany

We develop a theory of magnetooscillations in the photoconductivity of a two-dimensional electron gas observed in recent experiments. The effect is governed by a change of the electron distribution function induced by the microwave radiation. We analyze a nonlinearity with respect to both the dc field and the microwave power, as well as the temperature dependence determined by the inelastic relaxation rate.

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Recent experiments have discovered [1] that the resistivity of a high-mobility two-dimensional electron gas (2DEG) in GaAs/AlGaAs heterostructures subjected to microwave radiation of frequency ω exhibits magnetooscillations governed by the ratio ω/ω_c, where ω_c is the cyclotron frequency. Subsequent work [2–6] has shown that for samples with a very high mobility and for high radiation power the minima of the oscillations evolve into zero-resistance states (ZRS).

These spectacular observations have attracted much theoretical interest. As was shown in Ref. [7], the ZRS can be understood as a direct consequence of the oscillatory photoconductivity (OPC), provided that the latter may become negative. A negative value of the OPC signifies an instability leading to the formation of spontaneous-current domains showing zero value of the observable resistance. Therefore, the identification of the microscopic mechanism of the OPC appears to be the key question in the interpretation of the data [1–6].

A mechanism of the OPC proposed in Ref. [8] is based on the effect of microwave radiation on electron scattering by impurities in a strong magnetic field (see also Ref. [9] for an earlier theory and Ref. [10] for a systematic theory). An alternative mechanism of the OPC was recently proposed in Ref. [11]. In contrast to Refs. [8–10], this mechanism is governed by a radiation-induced change of the electron distribution function. Because of the oscillations of the density of states (DOS), $\nu(\varepsilon)$, related to the Landau quantization, the correction to the distribution function acquires an oscillatory structure as well. This generates a contribution to the dc conductivity which oscillates with varying ω/ω_c. A distinctive feature of the contribution of Ref. [11] is that it is proportional to the inelastic relaxation time τ_{in}. A comparison of the results of Refs. [10] and [11] shows that the latter contribution dominates if $\tau_{in} \gg \tau_q$ (where τ_q is the quantum, or single-particle, relaxation time due to impurity scattering), which is the case for the experimentally relevant temperatures.

The consideration of Ref. [11] is restricted to the regime which is linear in both the ac power and the dc electric field. The purpose of this paper is to develop a complete theory of the OPC governed by this mechanism, including nonlinear effects. We will demonstrate that the conductivity at a minimum becomes negative for a large microwave power and that a positive sign is restored for a strong dc bias, as it was assumed in Ref. [7].

We consider a 2DEG (mass m, density n_e, Fermi velocity v_F) subjected to a transverse magnetic field $B = (mc/e)\omega_c$. We assume that the field is classically strong, $\omega_c\tau_{tr} \gg 1$, where τ_{tr} is the transport relaxation time at $B = 0$. The photoconductivity σ_{ph} determines the longitudinal current flowing in response to a dc electric field E_{dc}, $j \parallel E_{dc} = \sigma_{ph}E_{dc}^2$, in the presence of a microwave electric field $E_\omega \cos\omega t$. The more frequently measured [1–3,5,6] longitudinal resistivity, ρ_{ph}, is given by $\rho_{ph} \simeq \rho_{xy}^2\sigma_{ph}$, where $\rho_{xy} \simeq eB/n_ec$ is the Hall resistivity, affected only weakly by the radiation.

We start with the formula for the dc conductivity:

$$\sigma_{ph} = 2\int d\varepsilon\, \sigma_{dc}(\varepsilon)\,[-\partial_\varepsilon f(\varepsilon)], \qquad (1)$$

where $f(\varepsilon)$ is the electron distribution function, and $\sigma_{dc}(\varepsilon)$ determines the contribution of electrons with energy ε to the dissipative transport. In the leading approximation [10,11], $\sigma_{dc}(\varepsilon) = \sigma_{dc}^D\nu^2(\varepsilon)$, where $\nu(\varepsilon) = \rho(\varepsilon)/\rho_0$ is the dimensionless DOS, $\rho_0 = m/2\pi$ is the DOS per spin at zero B (we use $\hbar = 1$), and $\sigma_{dc}^D = e^2\rho_0 v_F^2/2\omega_c^2\tau_{tr}$ is the dc Drude conductivity per spin. All interesting effects are due to a non-trivial energy dependence of the non-equilibrium distribution function $f(\varepsilon)$. The latter is found as a solution of the stationary kinetic equation

$$E_\omega^2\frac{\sigma^D(\omega)}{2\omega^2\rho_0}\sum_{\pm}\nu(\varepsilon \mp \omega)[f(\varepsilon \mp \omega) - f(\varepsilon)] + E_{dc}^2\frac{\sigma_{dc}^D}{\rho_0\nu(\varepsilon)}\frac{\partial}{\partial\varepsilon}\nu^2(\varepsilon)\frac{\partial}{\partial\varepsilon}f(\varepsilon) = \frac{f(\varepsilon) - f_T(\varepsilon)}{\tau_{in}}; \qquad (2)$$

where the ac Drude conductivity per spin is given by (we assume $|\omega - \omega_c|\tau_{tr} \gg 1$)

$$\sigma^D(\omega) = \sum_{\pm}\frac{e^2\rho_0 v_F^2}{4\tau_{tr}(\omega \mp \omega_c)^2}. \qquad (3)$$

On the right-hand side of Eq. (2), inelastic processes are included in the relaxation time approximation (more detailed discussion of the relaxation time τ_{in} is relegated to the end of the paper), and $f_T(\varepsilon)$ is the Fermi distribution. The left-hand side is due to the electron collisions with impurities in the presence of the external electric fields. The first term describes the absorption and emission of microwave quanta; the rate of these transitions was calculated in Ref. [11]. This term can be also extracted from the kinetic equation of Ref. [10]. The second term describes the effect of the dc field and can be obtained from the first one by taking the limit $\omega \to 0$.

Equation (2) suggests convenient dimensionless units for the strength of the ac and dc fields:

$$P_\omega = \frac{\tau_{in}}{\tau_{tr}} \left(\frac{eE_\omega v_F}{\omega}\right)^2 \frac{\omega_c^2+\omega^2}{(\omega^2-\omega_c^2)^2}; \qquad (4a)$$

$$Q_{dc} = \frac{2\tau_{in}}{\tau_{tr}} \left(\frac{eE_{dc}v_F}{\omega_c}\right)^2 \left(\frac{\omega}{\omega_c}\right)^2 : \qquad (4b)$$

Note that P_ω and Q_{dc} are proportional to τ_{in} and are infinite in the absence of inelastic relaxation processes.

We consider first the case of overlapping Landau levels (LLs), with the DOS given by $\nu = 1 - 2\lambda\cos\frac{2\pi\varepsilon}{\omega_c}$, where $\lambda = \exp(-\pi/\omega_c\tau_q) \ll 1$. Here τ_q is the zero-B single-particle relaxation time, which is much shorter than the transport time in high-mobility structures, $\tau_q \ll \tau_{tr}$ (because of the smooth character of a random potential of remote donors). The existence of a small parameter simplifies solution of the kinetic equation (2). To first order in λ, we look for a solution in the form

$$f = f_0 + f_{osc} + O(\lambda^2); \quad f_{osc} = \mathrm{Re}\left[f_1(\varepsilon)e^{i2\pi\varepsilon/\omega_c}\right] : \qquad (5)$$

We assume that the electric fields are not too strong [$P_\omega(\omega/T)^2 \ll 1$ and $Q_{dc}(\omega_c/T)^2 \ll 1$], so that the smooth part $f_0(\varepsilon)$ is close to the Fermi distribution $f_T(\varepsilon)$ at a bath temperature $T \gg \omega_c$; otherwise, the temperature of the electron gas is further increased due to heating. Smooth functions $f_{0,1}(\varepsilon)$ change on a scale of the order of temperature. We obtain

$$f_{osc}(\varepsilon) = -\frac{\omega_c}{2}\frac{\partial f_T}{\partial\varepsilon}\sin\frac{2\pi\varepsilon}{\omega_c}\,\frac{P_\omega\frac{2\omega}{\omega_c}\sin\frac{2\omega}{\omega_c} + 4Q_{dc}}{1+P_\omega\sin^2\frac{\omega}{\omega_c}+Q_{dc}} \qquad (6)$$

and substitute Eq. (6) into Eq. (1). Performing the energy integration in Eq. (1), we assume (in conformity with the experiment) that T is much larger than the Dingle temperature, $T \gg 1/2\tau_q$. The terms of order λ in Eq. (1) are exponentially suppressed $\int d\varepsilon\,\partial_\varepsilon f_T\cos\frac{2\pi\varepsilon}{\omega_c} \propto \exp(-2\pi^2 T/\omega_c) \ll \lambda^2$ and can be neglected. The leading ω dependent contribution to ρ_{ph} comes from the λ^2 term generated by the product of $\partial_\varepsilon f_{osc}(\varepsilon) \propto \cos\frac{2\pi\varepsilon}{\omega_c}$ and the oscillatory part $2\lambda\cos\frac{2\pi\varepsilon}{\omega_c}$ of $\tilde{R}(\varepsilon)$. This term does survive the energy averaging, $\int d\varepsilon\,\partial_\varepsilon f_T\cos^2\frac{2\pi\varepsilon}{\omega_c} \simeq -1/2$. We thus find

$$\frac{\rho_{ph}}{\rho^D_{dc}} = 1 + 2\lambda^2\left[1 - \frac{P_\omega\frac{2\omega}{\omega_c}\sin\frac{2\omega}{\omega_c} + 4Q_{dc}}{1+P_\omega\sin^2\frac{\omega}{\omega_c}+Q_{dc}}\right] : \qquad (7)$$

Equation (7) is our central result. It describes the photoconductivity in the regime of overlapping LLs, including all non-linear (in E_ω and E_{dc}) effects. Let us analyze it in more detail. In the linear-response regime ($E_{dc} \to 0$) and for a not too strong microwave field, Eq. (7) yields a correction to the dark dc conductivity $\sigma_{dc} = \sigma^D_{dc}(1+2\lambda^2)$ which is linear in the microwave power:

$$\frac{\rho_{ph} - \rho_{dc}}{\rho_{dc}} = -4\lambda^2 P_\omega\,\frac{\omega}{\omega_c}\sin\frac{2\omega}{\omega_c}; \qquad (8)$$

in agreement with Ref. [11]. It is enlightening to compare Eq. (8) with the contribution of the effect of the ac field on the impurity scattering [8–10]. The analytic result, Eq. (6.11) of Ref. [10], in the notation of Eq. (4) is

$$\frac{\rho^{[10]}_{ph} - \rho_{dc}}{\rho_{dc}} = -12\frac{\tau_q}{\tau_{in}}\lambda^2 P_\omega\left[\frac{\omega}{\omega_c}\sin\frac{2\omega}{\omega_c} + \sin^2\frac{\omega}{\omega_c}\right] :$$

This result has a similar frequency dependence as Eq. (8); however, its amplitude is much smaller at $\tau_{in} \gg \tau_q$, i.e., the mechanism of Refs. [8–10] appears to be irrelevant. Physically, the effect of the ac field on the distribution function is dominant because it is accumulated during a diffusive process of duration τ_{in}, whereas Refs. [8–10] consider only one scattering event.

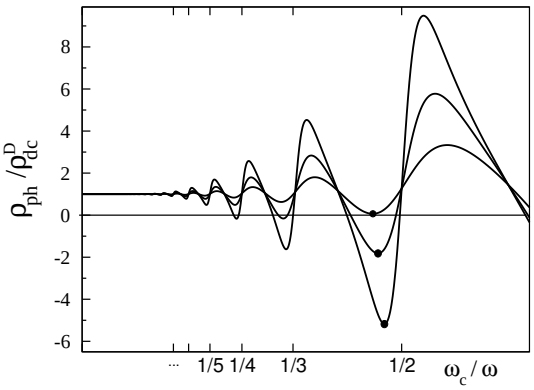

FIG. 1. Photoresistivity (normalized to the dark Drude value) for overlapping Landau levels vs ω_c/ω at fixed $\omega_\tau = 2\pi$. The curves correspond to different levels of microwave power $P_\omega^{(0)} = \{0.24; 0.8; 2.4\}$. Nonlinear I–V characteristics at the marked minima are shown in Fig. 2.

With increasing microwave power, the photoconductivity saturates at the value

$$\frac{\rho_{ph}}{\rho_{dc}} = 1 - 8\lambda^2\frac{\omega}{\omega_c}\cot\frac{\omega}{\omega_c}; \quad P_\omega\sin^2\frac{\omega}{\omega_c} \gg 1: \qquad (9)$$

Note that although the correction is proportional to $\lambda^2 \ll 1$, the factor $8(\omega/\omega_c)\cot(\omega/\omega_c)$ is large in the

vicinity of the cyclotron resonance harmonics $\omega = k\omega_c$ ($k = 1,2,\ldots$), and allows the photo-induced correction to exceed in magnitude the dark conductivity σ_{dc}. In particular, σ_{ph} around minima becomes negative at $P_\omega > P_\omega > 0$, with the threshold value given according to Eq. (7) by $P_\omega = 4\pi^2\frac{\omega}{\omega_c}\sin\frac{2\pi\omega}{\omega_c}\left(\sin^2\frac{\pi\omega}{\omega_c}\right)^{-1}$. The evolution of a B dependence of the photoresistivity ρ_{ph} with increasing microwave power $P_\omega^{(0)} = P_\omega(\omega_c = 0)$ is illustrated in Fig. 1.

Let us now $x = \omega/\omega_c$ such that $P_\omega > 0$, and consider the dependence of σ_{ph} on the dc field E_{dc} at $P_\omega > P_\omega$. As follows from Eq. (7), in the limit of large E_{dc} the conductivity is close to the Drude value and thus positive, $\sigma_{ph} = (1 - 6\pi^2)\sigma_{dc}^D > 0$. Therefore, σ_{ph} changes sign at a certain value E_{dc} of the dc field, which is determined by the condition $Q_{dc} = (P_\omega - P_\omega)/P_\omega$, see Fig. 2. The negative-conductivity state at $E_{dc} < E_{dc}$ is unstable with respect to the formation of domains with a spontaneous electric field of the magnitude E_{dc} [7].

Using Eqs. (4), we obtain

$$E_{dc} = \sqrt{E_\omega^2 - (E_\omega)^2}\left[\frac{\omega_c^4(\omega^2+\omega_c^2)}{2\omega^2(\omega^2-\omega_c^2)^2}\right]^{1/2} \frac{1}{\pi}\mathrm{Re}\left[4\pi^2\frac{\omega}{\omega_c}\sin\frac{2\pi\omega}{\omega_c}\left(\sin^2\frac{\pi\omega}{\omega_c}\right)^{-1}\right]^{1/2}; \quad (10)$$

with E_ω being the threshold value of the ac field at which the zero-resistance state develops. Equation (10) relates the electric field formed in the domain (measurable by local probe [6]) with the excess power of microwave radiation. It is worth noticing that this relation does not include the rate of the inelastic processes.

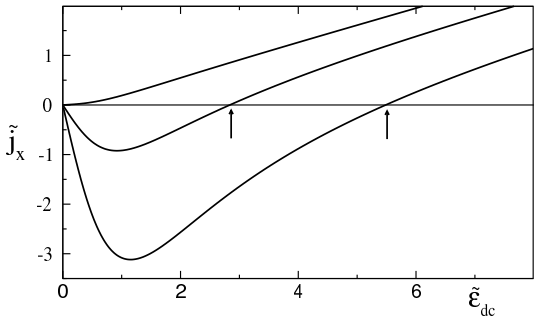

FIG. 2. Current–voltage characteristics [dimensionless current $\tilde{j}_x = (\sigma_{ph}/\sigma_{dc}^D)\tilde{E}_{dc}$ vs dimensionless field $\tilde{E}_{dc} = Q_{dc}^{1/2}$] at the points of minima marked by the circles in Fig. 1. The arrows show the dc field E_{dc} in spontaneously formed domains.

We now turn to the regime of strong B, $\omega_c \tau_q/\pi \gg 1$, where the LLs get separated. The DOS is then given (within the self-consistent Born approximation) by a sequence of semicircles of width $2\Gamma = 2(2\omega_c/\pi\tau_q)^{1/2}$:

$$\nu(\varepsilon) = \frac{2\omega_c}{\pi^2}\sum_n \mathrm{Re}\sqrt{\Gamma^2 - (\varepsilon - n\omega_c + \omega_c/2)^2}. \quad (11)$$

We use Eqs. (1) and (2) to evaluate the OPC at $Q_{dc} \ll 1$ to first order in P_ω and estimate the correction of the second order. We obtain

$$\frac{\sigma_{ph}}{\sigma_{dc}^D} = \frac{16\omega_c}{3\pi^2}\left(1 - P_\omega\frac{\omega}{\omega_c}\right)^{-1/2}\left[\sum_n \frac{\omega}{\omega - n\omega_c} + O\left(\frac{\omega_c P_\omega}{\omega}\right)\right]; \quad (12)$$

$$\chi(x) = \frac{3x}{4}\mathrm{Re}\left[\arccos(|x|-1) - \frac{1-|x|}{3}\right]\sqrt{|x|(2-|x|)}.$$

The photoresitivity for the case of separated LLs, Eq. (12), is shown in Fig. 3 for several values P_ω of the microwave power. Notice that a correction to Eq. (12) of second order in P_ω is still small even at $P_\omega > P_\omega = 2\pi^2/\omega\tau_q$, since $\omega_c P_\omega/\pi = 2\omega_c/\omega\tau_q \ll 1$. This means that it suffices to keep the linear-in-P_ω term only even for the microwave power at which the linear-response resistance becomes negative.

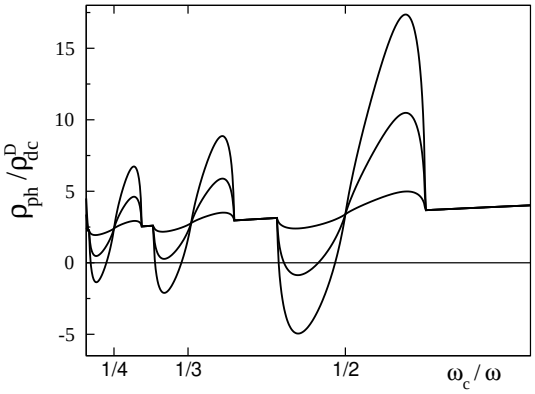

FIG. 3. Photoresistivity (normalized to the dark Drude value) for separated Landau levels vs ω_c/ω at fixed $\omega\tau_q = 16\pi$. The curves correspond to different levels of microwave power $P_\omega^{(0)} = \{0.004; 0.02; 0.04\}$.

As in the case of overlapping LLs, a negative value of the linear-response conductivity signals an instability leading to the formation of domains with the field E_{dc} at which $\sigma_{ph}(E_{dc}) = 0$. It turns out, however, that for separated LLs the kinetic equation in the form of Eq. (2) yields zero (rather than expected positive) conductivity in the limit of strong E_{dc}. This happens because elastic impurity scattering between LLs, inclined in a strong dc field, is not included in Eq. (2). The inter-LL transitions become efficient in dc fields as strong as $E_{dc} \sim (\omega_c/\tau_q)^{1/2}\omega_c^2/ev_F$ [10], which actually gives the strength of the field in domains.

Finally, we calculate the inelastic relaxation time τ_{in}. Of particular importance is its T dependence which in turn determines that of σ_{ph}. At not too high T, the dominant mechanism of inelastic scattering is due to electron-electron (e-e) collisions. It is worth emphasizing that the

e-e scattering does not yield relaxation of the total energy of the 2DEG and as such cannot establish a steady-state dc photoconductivity. That is to say the smearing of $f_0(\varepsilon)$ in Eq. (5), which is a measure of the degree of heating, is governed by electron-phonon scattering. However, the e-e scattering at $T \sim \omega_c$ does lead to relaxation of the oscillatory term f_{osc} [Eq. (6)] and thus determines the T behavior of the oscillatory contribution to σ_{ph}.

Quantitatively, the effect of electron-electron interaction is taken into account by replacing the right-hand side of Eq. (2) by $St_{ee}\{f\}$, where the collision integral $St_{ee}\{f\}$ is given by

$$St_{ee}\{f\} = \int d\varepsilon' \int dE\, A(E)\, \tilde{\nu}(\varepsilon_+)\, \tilde{\nu}(\varepsilon')\, \tilde{\nu}(\varepsilon'_+) \qquad (13)$$

$$\{f(\varepsilon) f_h(\varepsilon_+) f(\varepsilon') f_h(\varepsilon'_+) + f_h(\varepsilon) f(\varepsilon_+) f_h(\varepsilon') f(\varepsilon'_+)\},$$

and $f_h(\varepsilon) \equiv 1 - f(\varepsilon)$, $\varepsilon_+ = \varepsilon + E$, $\varepsilon' = \varepsilon' - E$. The function $A(E)$ describes the dependence of the matrix element of the screened Coulomb interaction on the transferred energy E,

$$A(E) = \frac{1}{2\varepsilon_F} \ln \frac{\varepsilon_F}{\max\{E, \omega_c(\omega_c\tau_{tr})^{1/2}, (\omega_c\tau_{tr})^{1/2}\}},$$

where ε_F is the Fermi energy. Thus $A(E)$ differs from the corresponding dependence for a clean 2DEG at zero B only by a change in the argument of the logarithm (a more detailed discussion will be given elsewhere).

We linearize the collision integral and solve Eq. (2). For overlapping LLs, we put $\tilde{\nu} = 1$ in accord with the accuracy of Eq. (7). Then only out-scattering processes contribute to the relaxation of the oscillatory part of the distribution function (6); the result is obtained by replacing $\tau_{in}^{-1} \to \tau_{ee}^{-1}(\varepsilon, T)$ in Eq. (2) with [12]

$$\frac{1}{\tau_{ee}} = \frac{\pi^2 T^2 + \varepsilon^2}{4\varepsilon_F} \ln \frac{\varepsilon_F}{\max\{T, \omega_c(\omega_c\tau_{tr})^{1/2}\}}. \qquad (14)$$

We turn now to the case of separated LLs. In this case, due to oscillation of $\tilde{\nu}$, even the linearized collision integral gives rise to a non-trivial integral operator. Analytical solution of the kinetic equation with this collision operator does not seem feasible. However, up to a factor of order unity, we can replace the exact collision integral with the relaxation-time approximation, thus returning to Eq. (2) with

$$\frac{1}{\tau_{in}} \sim \frac{\omega_c}{\pi} \frac{T^2}{\varepsilon_F} \ln \frac{\varepsilon_F}{\max\{T, (\omega_c\tau_{tr})^{1/2}\}}. \qquad (15)$$

One sees that in both cases of overlapping and separated LLs the inelastic relaxation rate is proportional to T^2, so that the OPC $\sigma_{ph} \propto \sigma_{dc}$ in the linear-in-P_ω regime [Eqs. (8), (12)] scales as T^2.

Our results are in overall agreement with the experimental findings [2,3]. The observed T dependence of the photoresistivity at maxima compares well with the predicted T^2 behavior. Typical parameters $\omega/2\pi \sim 50$–100 GHz, $\tau_q \sim 10$ ps yield $\omega\tau_q/2\pi \sim 0.5$–$1$ (overlapping LLs), and the experimental data indeed closely resemble Fig. 1. For $T \sim 1$ K and $\varepsilon_F \sim 100$ K we find $\tau_{in}^{-1} \sim 10$ mK, much less than $\tau_q^{-1} \sim 1$ K, as assumed in our theory. Finally, for the microwave power ~ 1 mW and the sample area ~ 1 cm^2, we estimate the dimensionless power $P_\omega^{(0)} \sim 0.005$–$0.1$, which agrees with characteristic values for separated LLs (Fig. 3) but is noticeably less than the prediction for overlapping LLs (Fig. 1). The reason for this discrepancy remains to be clarified.

To summarize, we have presented a theory of magnetooscillations in the photoconductivity of a 2DEG. The parametrically largest contribution to the effect is governed by the microwave-induced change in the distribution function. We have analyzed the nonlinearity with respect to both the microwave and dc fields. The result takes an especially simple form in the regime of overlapping LLs, Eq. (7). We have shown that the magnitude of the effect governed by the inelastic relaxation time increases as T^{-2} with lowering temperature.

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[*] Also at A.F. Ioffe Physico-Technical Institute, 194021 St. Petersburg, Russia.

[†] Also at Petersburg Nuclear Physics Institute, 188350 St. Petersburg, Russia.

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[12] The energy ε is counted in Eq. (14) from the Fermi level. The ε dependence of τ_{ee}^{-1} in Eq. (14) does not change the T^2 scaling (since the characteristic energy ε in Eq. (1) is of the order of T), but only yields a numerical factor. In particular, the inelastic time entering Eq. (8) is $\tau_{in} = 0.935\, \tau_{ee}(\varepsilon = 0, T)$.